

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
30 June 2005 (30.06.2005)

PCT

(10) International Publication Number
WO 2005/059990 A1

(51) International Patent Classification⁷: H01L 21/336,
G02F 1/1368, G09F 9/30, H01L 21/288, 21/3205, 29/786

(21) International Application Number:
PCT/JP2004/018076

(22) International Filing Date:
29 November 2004 (29.11.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2003-403733 2 December 2003 (02.12.2003) JP
2003-432083 26 December 2003 (26.12.2003) JP

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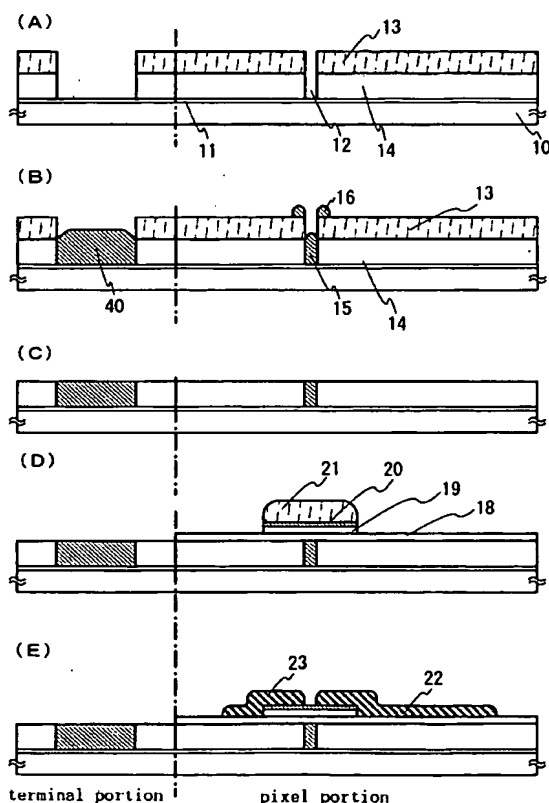
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(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD,
MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG,

[Continued on next page]

(54) Title: ELECTRONIC DEVICE AND SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME



(57) Abstract: It is conceivable that the problem that a signal is delayed by resistor of a wiring in producing a display which displays large area becomes remarkable. The present invention provides a manufacturing process using a droplet discharge method suitable for a large-sized substrate. In the present invention, after forming a base layer 11 (or base pretreatment) which enhances adhesiveness over a substrate in advance and forming an insulating film, a mask having a desired pattern shape is formed, and a desired depression is formed by using the mask. A metal material is filled in the depression having a mask 13 and a sidewall made from an insulating film by a droplet discharge method to form an embedded wiring (a gate electrode, a capacitor wiring, lead wiring or the like). Afterwards, it is flattened by a planarization processing, for example, a press or a CMP processing.



PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM,
TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM,
ZW.

SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ,
GW, ML, MR, NE, SN, TD, TG).

(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IS, IT, LU, MC, NL, PL, PT, RO, SE,

Published:

— with international search report

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ance Notes on Codes and Abbreviations" appearing at the begin-
ning of each regular issue of the PCT Gazette.